

2771-665

Section I. (Amendment to the Claims)

Please amend claims 1, 2, 19, 40, 41, and 65, withdraw claims 22-34, 40-41, 43-52 and 57-66, and cancel claims 3, 14-17, 35-39, 42 and 53-56, as set out below in the listing of claims 1-66 of the application.

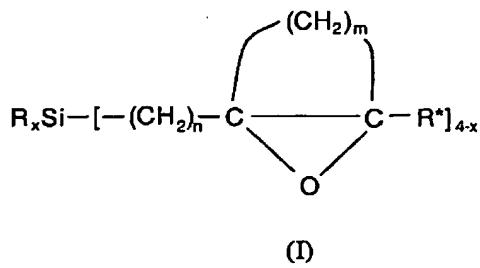
1. (Currently Amended) An organosilicon precursor for vapor deposition of a low k, high strength dielectric film, wherein the precursor comprises at least one of:

- (i) silicon-pendant oxiranyl functionality; and
- (ii) a disilyl moiety of the formula



wherein x is an integer having a value of from 0 to 4 inclusive.

2. (Currently Amended) The organosilicon precursor of claim 1, comprising a compound selected from the group consisting of oxiranylsilane compounds of formula (I) and disilane compounds of formula (III):



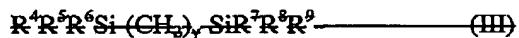
2771-665

wherein:

m is an integer having a value of 0 to 6, inclusive;

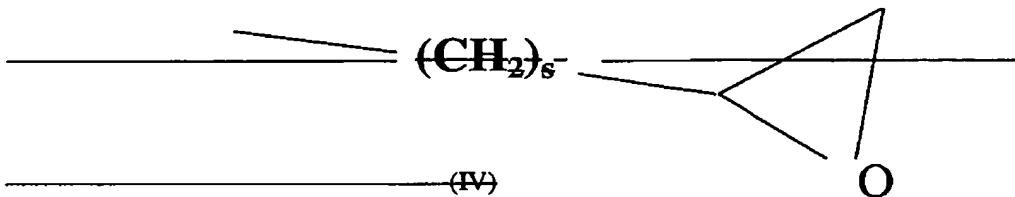
x is an integer having a value of 0 to 3, inclusive; and

each R and R^* can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl; and



wherein:

each of R^4 , R^5 , R^6 , R^7 , R^8 and R^9 can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, C₃-C₆ allyl, and exiranylalkylene of formula (IV)



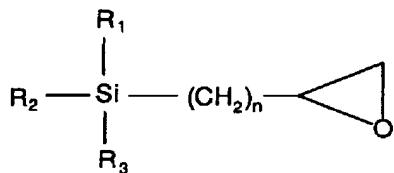
wherein s is 0 or 1; and

y is an integer having a value of from 0 to 4 inclusive.

2771-665

3. (Cancelled)

4. (Original) The organosilicon precursor of claim 1, having the formula (II):



(II)

wherein:

each of R_1 , R_2 and R_3 can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl; and

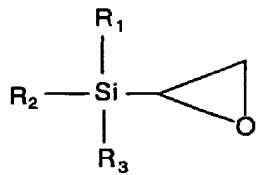
n is 0 or 1;

with the proviso that if $n = 1$, then one of R_1 , R_2 and R_3 alternatively can be



an oxiranyl functionality.

5. (Original) The organosilicon precursor of claim 1, having the formula (V):



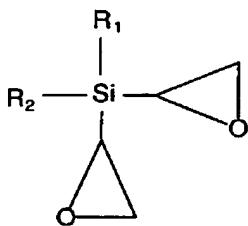
2771-665

(V)

wherein:

each of R₁, R₂ and R₃ is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl.

6. (Original) The organosilicon precursor of claim 1, having the formula (VI):

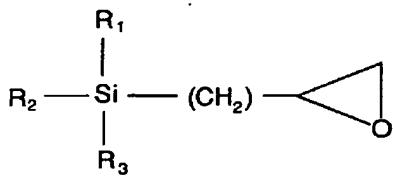


(VI)

wherein:

each of R₁ and R₂ is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl.

7. (Original) The organosilicon precursor of claim 1, having the formula (VII):



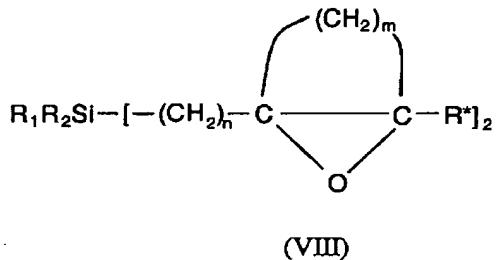
(VII)

2771-665

wherein:

each of R₁, R₂ and R^{*} is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl.

8. (Original) The organosilicon precursor of claim 1, having the formula (VIII):



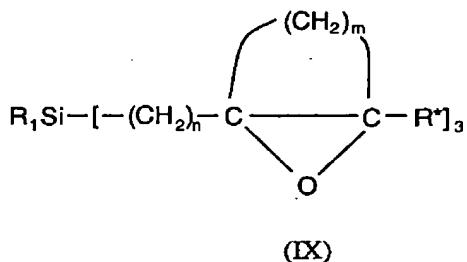
wherein:

m is an integer having a value of from 0 to 6 inclusive;

n is 0 or 1;

each R₁, R₂ and R^{*} can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl.

9. (Original) The organosilicon precursor of claim 1, having the formula (IX):



2771-665

wherein:

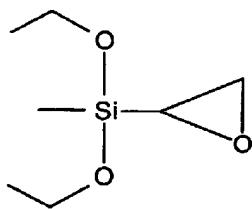
m is an integer having a value of from 0 to 6 inclusive;

n is 0 or 1;

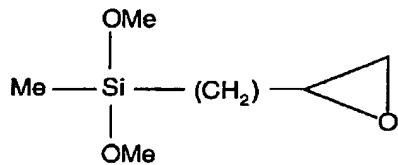
each of R₁ and R² can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl.

10. (Original) The organosilicon precursor of claim 1, selected from the group consisting of compounds of Formula (A), Formula (B) and Formula (C):

Formula (A), Me(EtO)₂SiCHCH₂O :

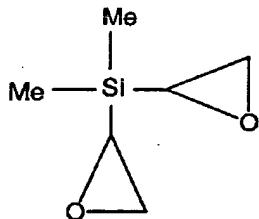


Formula (B), Me(MeO)₂Si CH₂CHCH₂O :



Formula (C), Me₂Si (CHCH₂O)₂ :

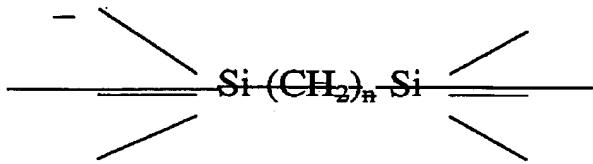
2771-665



wherein Me is methyl.

11. (Original) The organosilicon precursor of claim 10, having Formula (A).
12. (Original) The organosilicon precursor of claim 10, having Formula (B).
13. (Original) The organosilicon precursor of claim 10, having Formula (C).
- 14-17. (Cancelled)
18. (Original) The organosilicon precursor of claim 1, wherein the precursor further comprises TMCTS.
19. (Currently Amended) An organosilicon precursor composition for vapor deposition of a low k, high strength dielectric film, wherein the composition comprises:
 - (A) an organosilicon precursor comprising at least one of:
 - (i) silicon-pendant oxiranyl functionality; and

2771-665

(ii) a disilyl moiety of the formulawherein n is an integer having a value of from 0 to 4 inclusive; and

(B) a porogen.

20. (Original) The organosilicon precursor composition of claim 19, wherein said porogen is selected from the group consisting of compounds of the formula (X):



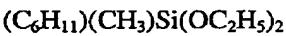
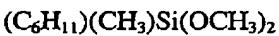
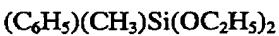
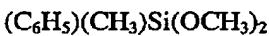
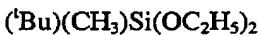
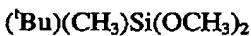
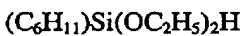
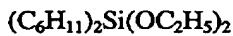
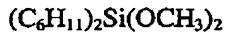
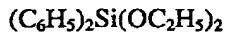
wherein:

each of R^{10} , R^{11} , R^{12} and R^{13} can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, and C₆-C₁₀ aryl, with the proviso that at least one of R^{10} , R^{11} , R^{12} and R^{13} is C₁-C₈ alkoxy.

21. (Original) The organosilicon precursor composition of claim 19, wherein said porogen is selected from the group consisting of:

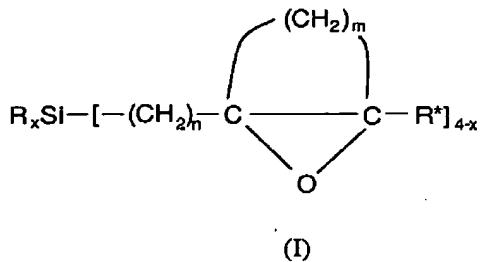


2771-665



wherein 'Bu is tertiary butyl.

22. (Withdrawn) A method of forming an oxiranylsilane compound of formula (I):



wherein:

2771-665

m is an integer having a value of 0 to 6, inclusive;

n is 0 or 1;

x is an integer having a value of 0 to 3, inclusive; and

each R and R' can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl,

said method comprising oxidizing a corresponding vinylsilane or allylsilane compound.

23. (Withdrawn) The method of claim 22, wherein the step of oxidizing comprises reaction with an oxidizing agent that is inert in relation to Si-OR fragments.

24. (Withdrawn) The method of claim 23, wherein said oxidizing agent comprises an agent selected from the group consisting of meta-Cl(C₆H₄)C(O)OOH, 'BuOOH, wherein 'Bu is tertiary butyl, and Me₃OOSiMe₃, wherein Me is methyl.

25. (Withdrawn) The method of claim 23, wherein said oxidizing agent comprises meta-Cl(C₆H₄)C(O)OOH.

26. (Withdrawn) The method of claim 22, wherein said step of oxidizing is conducted in a non-flammable solvent medium.

27. (Withdrawn) The method of claim 26, wherein said non-flammable solvent medium comprises dichloromethane.

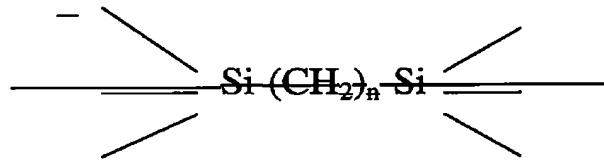
2771-665

28. (Withdrawn) The method of claim 26, wherein said non-flammable solvent medium comprises chloroform.
29. (Withdrawn) The method of claim 22, wherein said oxiranylsilane compound is $\text{Me}(\text{EtO})_2\text{SiCHCH}_2\text{O}$.
30. (Withdrawn) The method of claim 29, wherein said oxidizing step comprises Reaction (1).
31. (Withdrawn) The method of claim 22, wherein said oxiranylsilane is $\text{Me}(\text{MeO})_2\text{SiCH}_2\text{CHCH}_2\text{O}$.
32. (Withdrawn) The method of claim 31, wherein said oxidizing step comprises Reaction (2).
33. (Withdrawn) The method of claim 22, wherein said oxiranylsilane is $\text{Me}_2\text{Si}(\text{CHCH}_2\text{O})_2$.
34. (Withdrawn) The method of claim 33, wherein said oxidizing step comprises Reaction (3).
- 35-39. (Cancelled)

2771-665

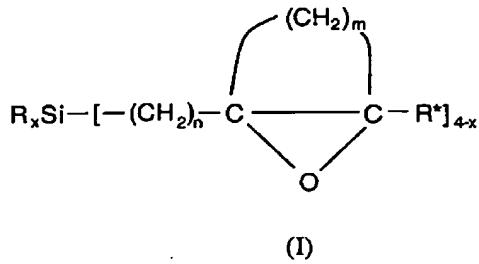
40. (Withdrawn) A method of forming a low k, high strength dielectric film on a substrate, comprising vapor depositing said film on the substrate from a precursor comprising at least one of:

- (i) silicon-pendant oxiranyl functionality; and
- (ii) a disiloxane moiety of the formula



wherein x is an integer having a value of from 0 to 4 inclusive.

41. (Withdrawn) The method of claim 40, wherein said precursor comprises a compound is selected from the group consisting of oxiranylsilane compounds of formula (I) and ~~and disilane compounds of formula (III)~~:



wherein:

m is an integer having a value of 0 to 6, inclusive;

x is an integer having a value of 0 to 3, inclusive; and

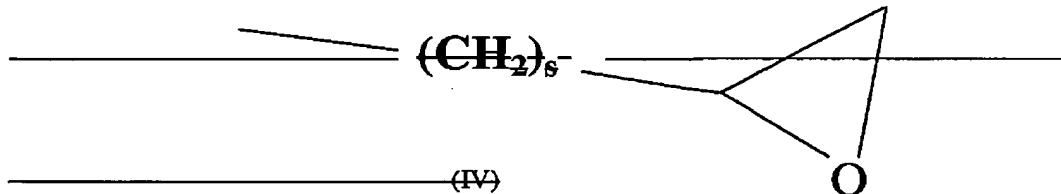
2771-665

each R and R^{*} can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl; and



wherein:

each of R⁴, R⁵, R⁶, R⁷, R⁸ and R⁹ can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₃-C₆ vinyl, C₃-C₆ allyl, and exiranylalkylene of formula (IV)



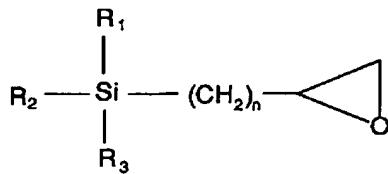
wherein s is 0 or 1; and

y is an integer having a value of from 0 to 4 inclusive.

42. (Cancelled)

2771-665

43. (Withdrawn) The method of claim 41, wherein the precursor comprises a compound having the formula (II):



(II)

wherein:

each of R_1 , R_2 and R_3 can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₃ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl; and

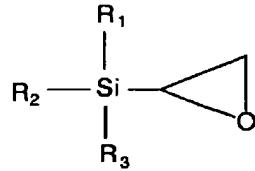
n is 0 or 1;

with the proviso that if $n = 1$, then one of R_1 , R_2 and R_3 alternatively can be



an oxiranyl functionality.

44. (Withdrawn) The method of claim 41, wherein the precursor comprises a compound having the formula (V):



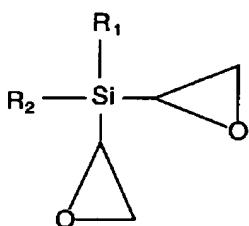
(V)

wherein:

2771-665

each of R₁, R₂ and R₃ is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl.

45. (Withdrawn) The method of claim 41, wherein the precursor comprises a compound having the formula (VI):

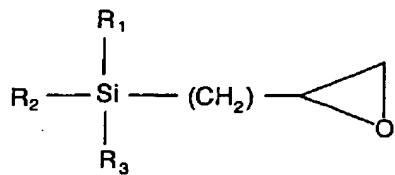


(VI)

wherein:

each of R₁ and R₂ is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl.

46. (Withdrawn) The method of claim 41, wherein the precursor comprises a compound having the formula (VII):



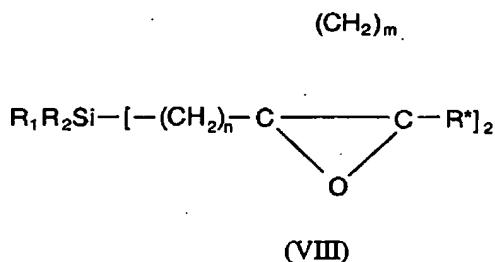
(VII)

2771-665

wherein:

each of R₁, R₂ and R₃ is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl.

47. (Withdrawn) The method of claim 41, wherein the precursor comprises a compound having the formula (VIII):



wherein:

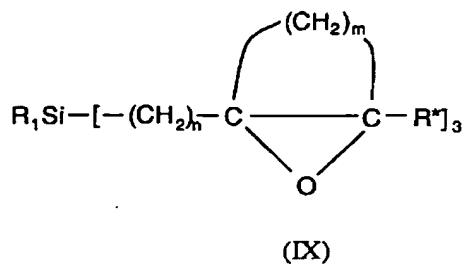
m is an integer having a value of from 0 to 6 inclusive;

n is 0 or 1;

each R₁, R₂ and R^{*} can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl.

48. (Withdrawn) The method of claim 41, wherein the precursor comprises a compound having the formula (IX):

2771-665



wherein:

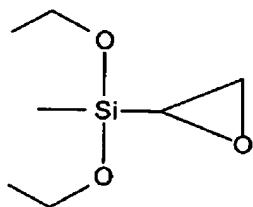
m is an integer having a value of from 0 to 6 inclusive;

n is 0 or 1;

each of R_1 and R^* can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₃-C₆ allyl.

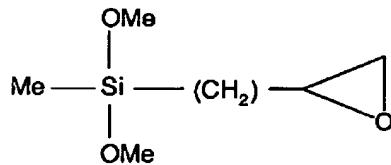
49. (Withdrawn) The method of claim 41, wherein the precursor comprises a compound selected from the group consisting of compounds of Formula (A), Formula (B) and Formula (C):

Formula (A), Me(EtO)₂SiCHCH₂O :

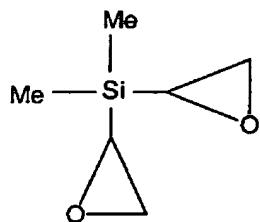


Formula (B), Me(MeO)₂Si CH₂CHCH₂O :

2771-665



Formula (C), $\text{Me}_2\text{Si}(\text{CHCH}_2\text{O})_2$:



wherein Me is methyl.

50. (Withdrawn) The method of claim 49, wherein the precursor comprises a compound of Formula (A).

51. (Withdrawn) The method of claim 49, wherein the precursor comprises a compound of Formula (B).

52. (Withdrawn) The method of claim 49, wherein the precursor comprises a compound of Formula (C).

53-56. (Cancelled)

2771-665

57. (Withdrawn) The method of claim 40, wherein said vapor depositing step comprises use of a porogen in combination with said precursor.

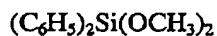
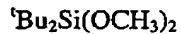
58. (Withdrawn) The method of claim 57, wherein said porogen is selected from the group consisting of compounds of the formula (X):



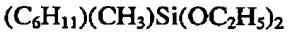
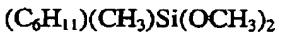
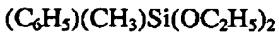
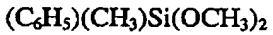
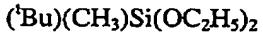
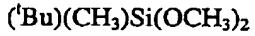
wherein:

each of R^{10} , R^{11} , R^{12} and R^{13} can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, and C₆-C₁₀ aryl, with the proviso that at least one of R^{10} , R^{11} , R^{12} and R^{13} is C₁-C₈ alkoxy.

59. (Withdrawn) The method of claim 57, wherein said porogen is selected from the group consisting of:



2771-665



wherein 'Bu is tertiary butyl.

60. (Withdrawn) The method of claim 40, wherein said vapor depositing step comprises chemical vapor deposition.

61. (Withdrawn) The method of claim 40, wherein said vapor depositing step comprises plasma-enhanced chemical vapor deposition.

62. (Withdrawn) The method of claim 40, wherein said vapor depositing step comprises flowing said precursor to a vapor deposition locus in a carrier gas.

63. (Withdrawn) The method of claim 62, wherein said carrier gas comprises carbon dioxide.

2771-665

64. (Withdrawn) The method of claim 62, wherein the precursor and the carrier gas are the only potential sources of oxygen at the vapor deposition locus.

65. (Withdrawn) The method of claim 40, wherein the precursor is selected from the group consisting of:

Me(EtO)₂SiCHCH₂O;

Me(MeO)₂Si CH₂CHCH₂O; and

Me₂Si (CHCH₂O)₂;

Me(MeO)₂SiCH₂CH₂SiMe(OMe)₂;

Me₂(MeO)SiCH₂CH₂SiMe₂(OMe); and

(MeO)₂SiCH₂Si(OMe)₂.

66. (Withdrawn) The method of claim 40, wherein the precursor further comprises TMCTS.